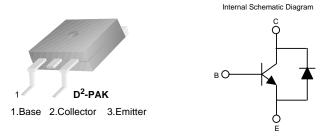


March 2012

# FJB3307D High Voltage Fast Switching NPN Power Transistor

### **Features**

- Built-in Diode between Collector and Emitter
- Suitable for Electronic Ballast and Switch Mode Power Supplies



## **Absolute Maximum Ratings** $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current (DC)	8	Α
I <sub>CP</sub>	* Collector Current (Pulse)	16	Α
Ι <sub>Β</sub>	Base Current (DC)	4	Α
I <sub>BP</sub>	I <sub>BP</sub> * Base Current (Pulse)		Α
T <sub>J</sub>	T <sub>J</sub> Junction Temperature		°C
T <sub>STG</sub>	Storage Temperature	-55 to 150	°C

<sup>\*</sup> Pulse Test: PW = 300µs, Duty Cycle = 2% Pulsed

### **Thermal Characteristics**

Symbol	Parameter		Value	Units	
P <sub>D</sub>	Total Device Dissipation	$T_a = 25$ °C $T_c = 25$ °C	1.72 80	W W	
$R_{ heta ja}$	Thermal Resistance, Junction to Ambient	72.5	°C/W		
$R_{ heta jc}$	Thermal Resistance, Junction to Case		1.56	°C/W	

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# **Electrical Characteristics** $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 500 \mu A, I_E = 0$	700			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	400			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	9			V
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			1	mA
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 2A$ $V_{CE} = 5V, I_{C} = 5A$	8 5		40 30	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 2A$ , $I_B = 0.4A$ $I_C = 5A$ , $I_B = 1A$ $I_C = 5A$ , $I_B = 1A$ , $T_a = 100$ °C $I_C = 8A$ , $I_B = 2A$			1 2 3 3	> > >
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 2A$ , $I_B = 0.4A$ $I_C = 5A$ , $I_B = 1A$ $I_C = 5A$ , $I_B = 1A$ , $T_a = 100$ °C			1.2 1.6 2	V V V
V <sub>F</sub>	Diode Forward Voltage	I <sub>C</sub> = 3A			2.5	V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		60		pF
t <sub>STG</sub>	Storage Time	V <sub>CC</sub> = 125V, I <sub>C</sub> = 5A			3	μS
t <sub>F</sub>	Fall Time	$I_{B1} = -I_{B2} = 1A, R_L = 50\Omega$			0.7	μS
t <sub>STG</sub>	Storage Time	$V_{CC} = 30V, I_C = 5A, L=200\mu H$ $I_{B1}=1A, R_{BB} = 0\Omega,$			2.3	μS
t <sub>F</sub>	Fall Time	$V_{BE(OFF)}$ = -5V, $V_{CLAMP}$ = 250V			150	ns

<sup>\*</sup> Pulse test: PW = 300μs, Duty Cycle = 2% Pulsed

# h<sub>FE</sub> Classification

Classification	H1	H2
h <sub>FE1</sub>	15 ~ 28	26 ~ 39

## **Typical Performance Characteristics**

Figure 1. Static Characteristic

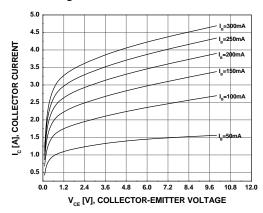


Figure 2. DC Current Gain

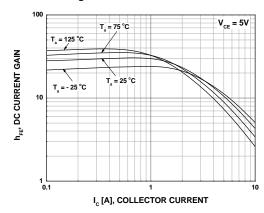


Figure 3. Collector-Emitter Saturation Voltage

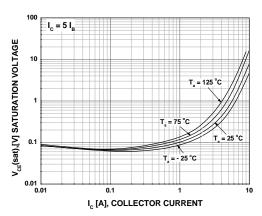


Figure 4. Base-Emitter Saturation Voltage

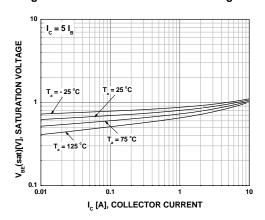


Figure 5. Collector Output Capacitance

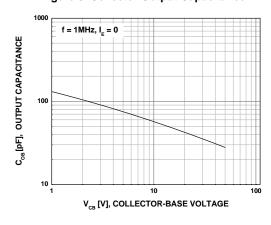
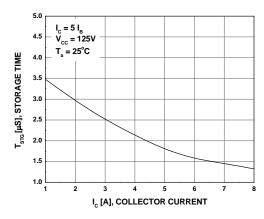


Figure 6. Storage Time (Resistive Load)



## **Typical Performance Characteristics (Continued)**

Figure 7. Fall Time (Resistive Load)

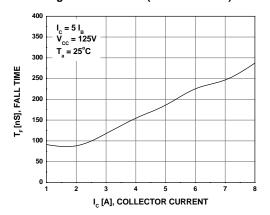


Figure 8. Storage Time (Inductive Load)

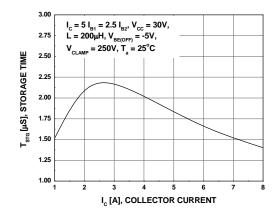


Figure 9. Fall Time (Inductive Load)

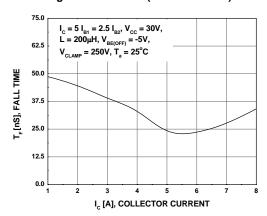


Figure 10. Power Derating

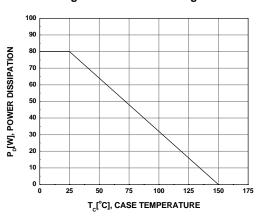


Figure 11. Reverse Bias Safe Operating Area

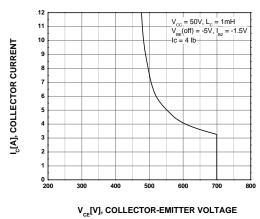
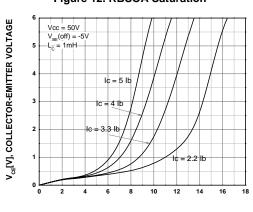


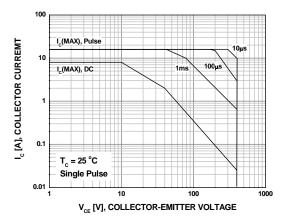
Figure 12. RBSOA Saturation



 $I_{CE}[A]$ , COLLECTOR CURRENT

## Typical Performance Characteristics (Continued)

Figure 13. Forward Biased Safe Operating Area



# **Physical Dimensions** D<sup>2</sup>-PAK 9 45 10.00 (6.40)1.78 MAX 3.80 3 1.05 - 5.08 LAND PATTERN RECOMMENDATION 0.25 M B AM UNLESS NOTED, ALL DIMS TYPICAL 5,08 6,22 MIN 6.86 MIN 15.88 14.61 SEE DETAIL A NOTES: UNLESS OTHERWISE SPECIFIED NOTES: UNLESS OTHERWISE SPECIFIED A) ALL DIMENSIONS ARE IN MILLIMETERS. B) REFERENCE JEDEC, TO-263, VARIATION AB. C) DIMENSIONING AND TOLERANCING PER ANSI Y14,5M - 1994, D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE). E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N F) FILENAME: TO263A02REV6 GAGE PLANE $0.74 \\ 0.33$ 0.25 ○ 0.10 B 0,25 MAX-SEATING DETAIL A, ROTATED 90° Dimensions in Millimeters

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